Hit List

First Hit | Clear | Generate Collection | Print | Fwd Refs | Bkwd Refs | Generate OACS

Search Results - Record(s) 1 through 10 of 10 returned.

☐ 1. Document ID: US 20070299169 A1

AB: A resin composition comprising: (1) 100 parts by weight of an aromatic polycarbonate resin (component A); (2) 0.005 to 0.6 part by weight of a fluorine-containing organic metal salt having a fluoride ion content measured by ion chromatography of 0.2 to 20 ppm in terms of weight (component B); and (3) at least one component selected from the group consisting of a flame retardant (component C), a fatty acid ester (component D), an ultraviolet light absorber (component E), polytetrafluoroethylene having fibril formability (component F), a filler (component G), a silicate mineral (component H) and a titanium dioxide pigment (component I). A process of manufacturing the resin compositon and a method of preventing the melt dripping during combustion of the resin composition. The flame retardancy of the above aromatic polycarbonate resin composition comprising the fluorine-containing organic metal salt compound is improved.

Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments | Claims | KWIC | Draw Des

☐ 2. Document ID: US 20070078213 A1

AB: The invention relates to fine particle hard molded bodies which provide increased abrasion resistance when embedded in polymer matrices. Said fine particle hard molded bodies comprise materials which have a hardness of .gtoreq.7 on Mohs' scale of hardness and form the molded body or are provided directly on a fine particle substrate in the form of one or several layers. Also disclosed are a method for producing the molded bodies and the use thereof in polymer matrices.

Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments | Claims | KWIC | Draw Des

☐ 3. Document ID: US 20060257662 A1

AB: The present invention relates to a process for the production of porous inorganic materials or a matrix material containing nanoparticles with high uniformity of thickness and/or high effective surface area and to the materials obtainable by this process. By the abovementioned process materials with a defined thickness in the region of .+-.10%, preferably .+-.5%, of the average thickness are available.

Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments | Claims | KWIC | Draw Des

☐ 4. Document ID: US 20050161678 A1

AB: A product produced in a PVD method is described, which consists of thin plane-parallel structures having a thickness in the range from 20 to 2000 nm and small dimensions in the range below one mm. Production is carried out by condensation of silicon suboxide onto a carrier passing by way of the vaporisers. The carrier is pre-coated, before condensation of the silicon suboxide, with a soluble, inorganic or organic separating agent in a PVD method. All steps, including that of detaching the product by dissolution, can be carried out continuously and simultaneously at different locations. As final step, the SiO.sub.y may be oxidised to SiO.sub.2 in an oxygen-containing gas at atmospheric pressure and temperatures of more than 200.degree. C. or SiO.sub.y may be converted to SiC at the surface of the plane-parallel structures in a carbon-containing gas at from 500.degree. C. to 1500.degree. C. The products produced in that manner are distinguished by high uniformity of thickness.

Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments | Claims | KWIC | Draw Des

☐ 5. Document ID: US 20040216388 A1

AB: A chemical-mechanical abrasive composition for use in semiconductor processing uses abrasive particles having a non-spherical morphology.

Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments | Claims | KWIC | Draw Des

☐ 6. Document ID: US 20020115011 A1

AB: In an image forming system, an image-bearing member having a photoconductor layer comprising an Si-based non-single crystal material is charged at a relatively low potential of 250 to 600 volts by a contact charging member in the presence of electroconductive fine powder. An electrostatic latent image formed on the image-bearing member is developed with a magnetic toner which includes magnetic toner particles comprising at least a binder resin and a magnetic iron oxide, and inorganic fine powder and electroconductive fine powder present at the surface of the magnetic toner particles. The magnetic toner has a weight-average particle size of 3-10 .mu.m and an average circularity of 0.950 to 0.995, and contains 0.05 to 3.00 % of isolated iron-containing particles.

Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments | Claims | KWIC | Draw Des

☐ 7. Document ID: US 7256425 B2

AB: A product produced in a PVD method is described, which consists of thin plane-parallel structures having a thickness in the range from 20 to 2000 nm and small dimensions in the range below one mm. Production is carried out by condensation of silicon suboxide onto a carrier passing by way of the vaporisers. The carrier is pre-coated, before condensation of the silicon suboxide, with a soluble, inorganic or organic separating agent in a PVD method. All steps, including that of detaching the product by dissolution, can be carried out continuously and simultaneously at different locations. As final step, the SiO.sub.y may be oxidised to SiO.sub.2 in an oxygen-containing gas at atmospheric pressure and temperatures of more than 200.degree. C. or SiO.sub.y may be converted to SiC at the surface of the plane-parallel structures in a carbon-containing gas at from 500.degree. C. to 1500.degree. C. The products produced in that manner are distinguished by high uniformity of thickness.

Full | Title | Citation | Front | Review | Classification | Date | Reference | | | Claims | KWIC | Draw Des

☐ 8. Document ID: US 7043175 B2

AB: In an image forming system, an image-bearing member having a photoconductor layer comprising an Si-based non-single crystal material is charged at a relatively low potential of 250 to 600 volts by a contact charging member in the presence of electroconductive fine powder. An electrostatic latent image formed on the image-bearing member is developed with a magnetic toner which includes magnetic toner particles comprising at least a binder resin and a magnetic iron oxide, and inorganic fine powder and electroconductive fine powder present at the surface of the magnetic toner particles. The magnetic toner has a weight-average particle size of 3-10 .mu.m and an average circularity of 0.950 to 0.995, and contains 0.05 to 3.00% of isolated iron-containing particles.

Full | Title | Citation | Front | Review | Classification | Date | Reference | | | Claims | KWIC | Draw Des

☐ 9. Document ID: US 5776235 A

AB: Thick opaque ceramic coatings are used to protect delicate microelectronic devices against excited energy sources, radiation, light, abrasion, and wet etching techniques. The thick opaque ceramic coating are prepared from a mixture containing phosphoric anhydride, i.e., phosphorous pentoxide (P.sub.2 O.sub.5), and a pre-ceramic silicon-containing material. It is preferred to also include tungsten carbide (WC) and tungsten metal (W) in the coating mixture. The coating is pyrolyzed to form a ceramic SiO.sub.2 containing coating. A second coating of plasma enhanced chemical vapor deposited (PECVD) silicon carbide (SiC), diamond, or silicon nitride (Si.sub.3 N.sub.4), can be applied over the thick opaque ceramic coating to provide hermeticity. These coatings are useful on patterned wafers, electronic devices, and electronic substrates. The

thick opaque ceramic coating is unique because it is resistant to etching using wet chemicals, i.e., acids such as H.sub.3 PO.sub.4 and H.sub.2 SO.sub.4, or bases.

Full | Title | Citation | Front | Review | Classification | Date | Reference | Claims | KWIC | Draw Des

☐ 10. Document ID: US 5730792 A

AB: Thick opaque ceramic coatings are used to protect delicate microelectronic devices against excited energy sources, radiation, light, abrasion, and wet etching techniques. The thick opaque ceramic coating are prepared from a mixture containing tungsten carbide (WC), tungsten metal (W), and phosphoric anhydride, i.e., phosphorous pentoxide (P.sub.2 O.sub.5), carried in an aqueous alkanol dispersion of colloidal silica and partial condensate of methylsilanetriol. The coating is pyrolyzed to form a ceramic SiO.sub.2 containing coating. A second coating of plasma enhanced chemical vapor deposited (PECVD) silicon carbide (SiC), diamond, or silicon nitride (Si.sub.3 N.sub.4), can be applied over the thick opaque ceramic coating to provide hermeticity. These coatings are useful on patterned wafers, electronic devices, and electronic substrates. The thick opaque ceramic coating is unique because the methyl silsesquioxane resin is resistant to etching using wet chemicals, i.e., acids such as H.sub.3 PO.sub.4 and H.sub.2 SO.sub.4, or bases.

Full | Title | Citation | Front | Review | Classification | Date | Reference | Claims | KWIC | Draw Des

Clear | Generate Collection | Print | Fwd Refs | Bkwd Refs | Generate OACS

Terms	Documents
L7 and CVD	10

Display Format: AB Change Format

Previous Page Next Page Go to Doc#